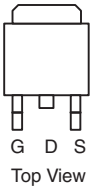
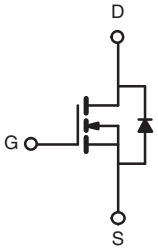
Automotive
N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0035
I_D (A)	100
Configuration	Single





N-Channel MOSFET

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified[d]
- Compliant to RoHS Directive 2002/95/EC

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM100N04-3m5-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C[a]	I_D	100	A
	T_C = 125 °C		87	
Continuous Source Current (Diode Conduction)[a]		I_S	100	
Pulsed Drain Current[b]		I_{DM}	400	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	70	
Single Pulse Avalanche Energy		E_{AS}	245	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	157	W
	T_C = 125 °C		52	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Junction-to-Ambient	PCB Mount[c]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.95	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR-4 material).
d. Parametric verification ongoing.

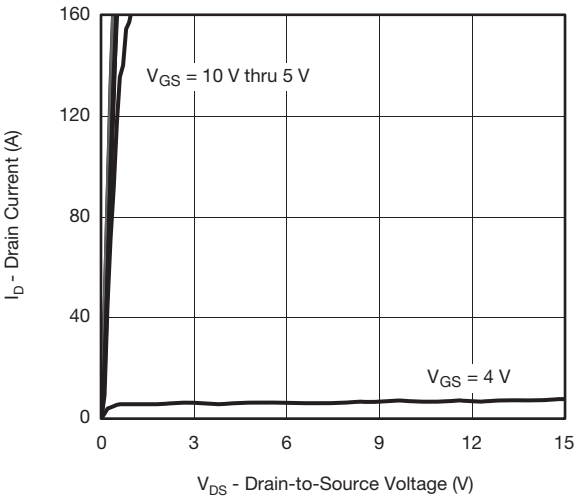
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA		40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.5	3.0	3.5	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 40 V	-	-	1.0	µA
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 40 V, T_J = 175 °C	-	-	250	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A	-	0.0022	0.0035	Ω
		V_{GS} = 10 V	I_D = 30 A, T_J = 125 °C	-	-	0.0057	
		V_{GS} = 10 V	I_D = 30 A, T_J = 175 °C	-	-	0.0070	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 30 A		-	201	-	S
Dynamic[b]							
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	6325	7910	pF
Output Capacitance	C_{oss}			-	744	930	
Reverse Transfer Capacitance	C_{rss}			-	314	395	
Total Gate Charge[c]	Q_g	V_{GS} = 10 V	V_{DS} = 20 V, I_D = 100 A	-	95.5	145	nC
Gate-Source Charge[c]	Q_{gs}			-	25.5	-	
Gate-Drain Charge[c]	Q_{gd}			-	14.7	-	
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 20 V, R_L = 0.2 Ω I_D ≅ 100 A, V_{GEN} = 10 V, R_g = 1 Ω		-	14	21	ns
Rise Time[c]	t_r			-	11	17	
Turn-Off Delay Time[c]	$t_{d(off)}$			-	48	72	
Fall Time[c]	t_f			-	9	14	
Source-Drain Diode Ratings and Characteristics[b]							
Pulsed Current[a]	I_{SM}			-	-	400	A
Forward Voltage	V_{SD}	I_F = 30 A, V_{GS} = 0 V		-	0.8	1.5	V

Notes

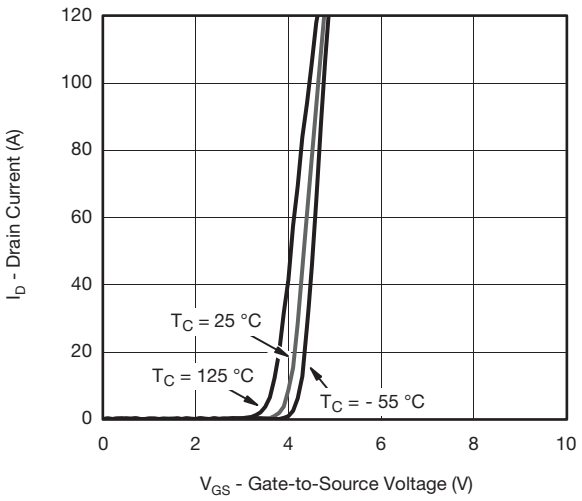
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

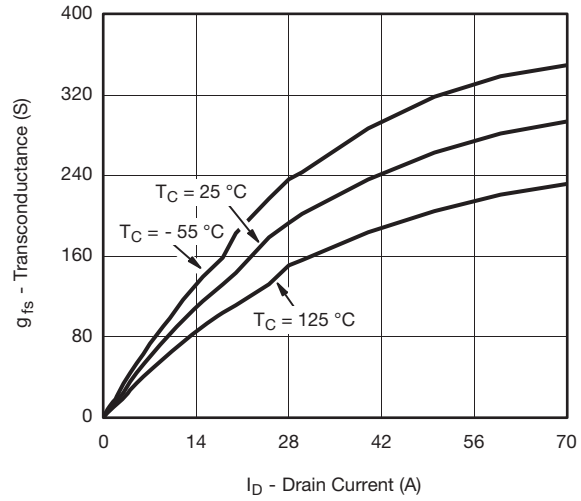
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



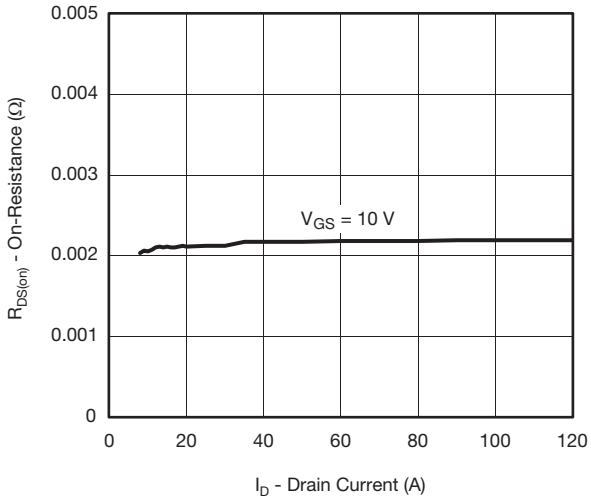
Output Characteristics



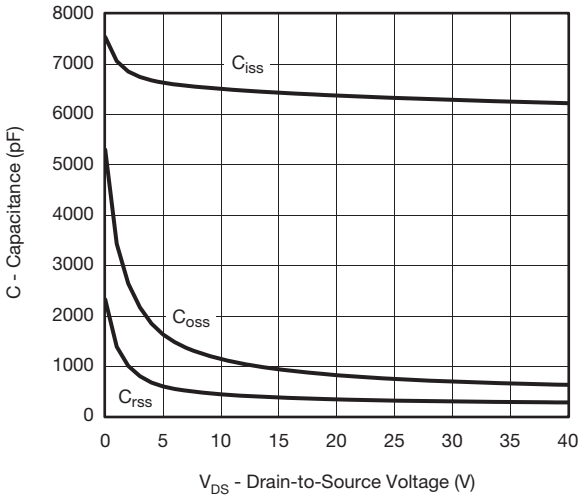
Transfer Characteristics



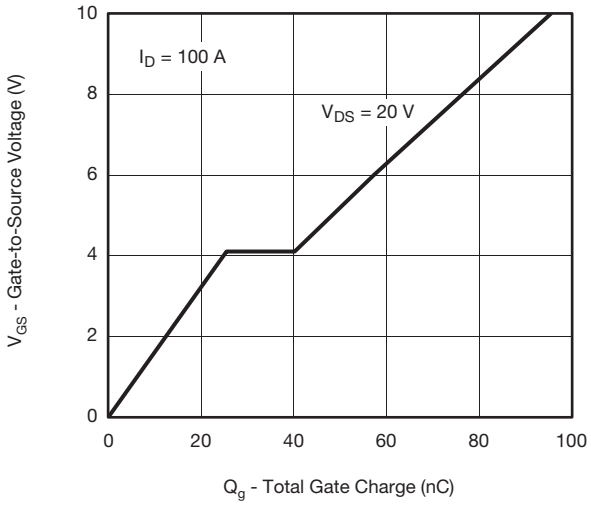
Transconductance



On-Resistance vs. Drain Current

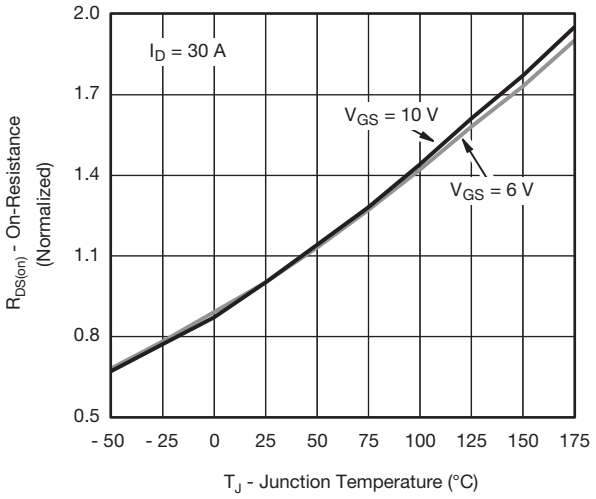


Capacitance

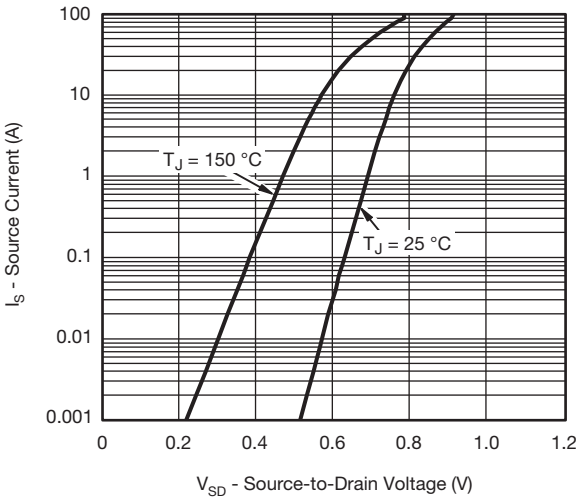


Gate Charge

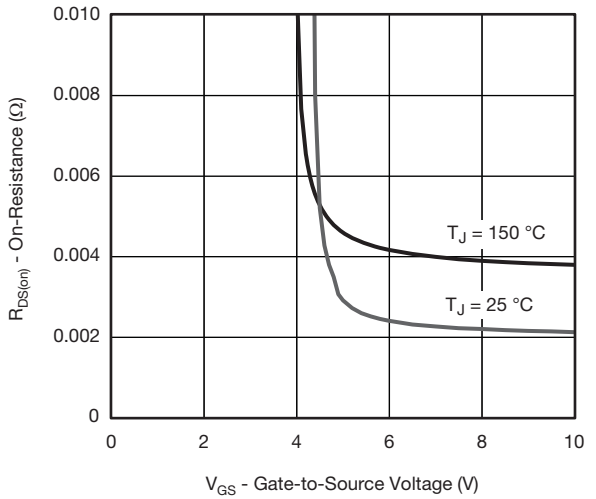
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



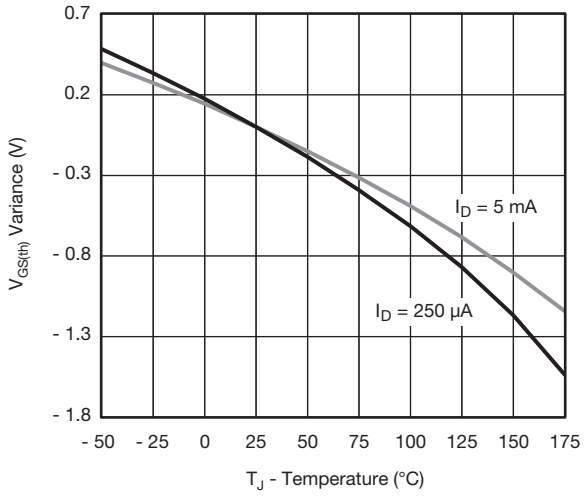
On-Resistance vs. Junction Temperature



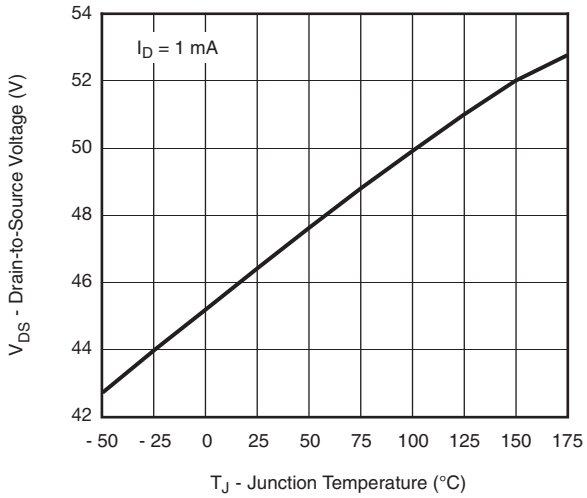
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

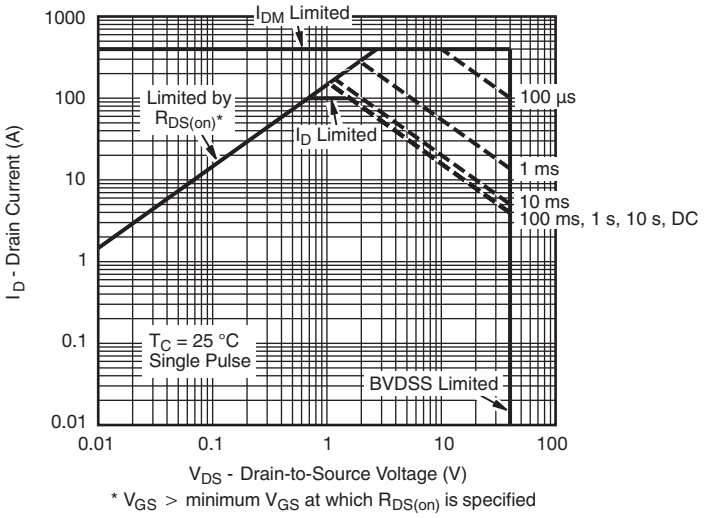


Threshold Voltage

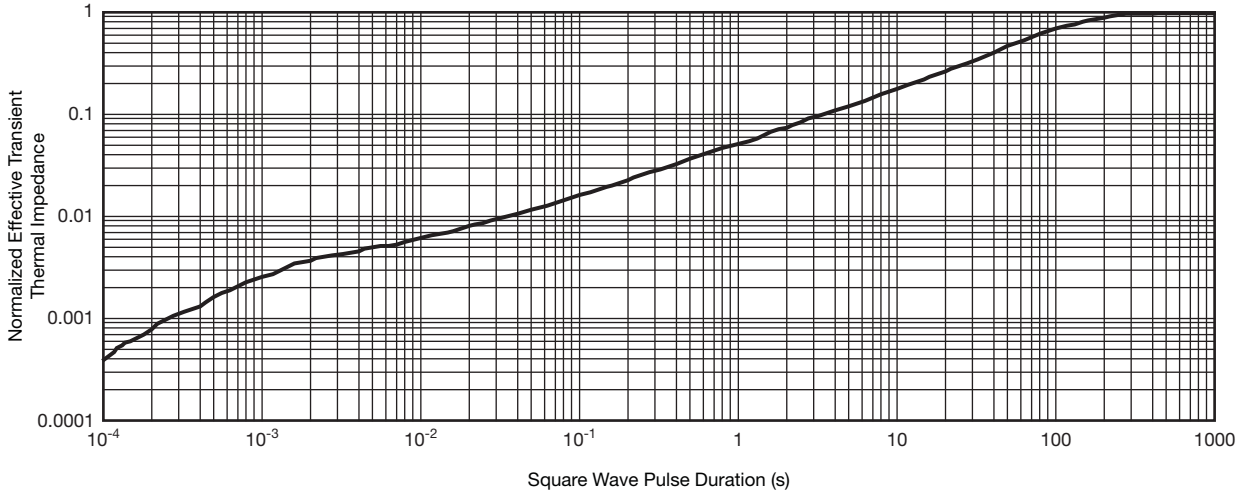


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

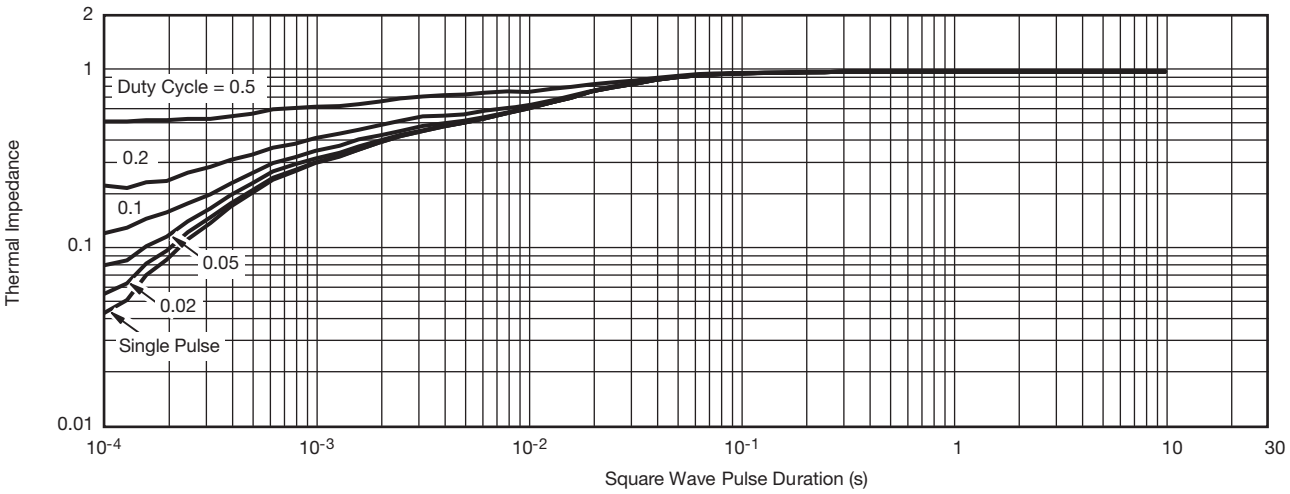


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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